

N-Channel Power MOSFET

30V, 55A, 8mΩ

FEATURES

- Fast switching
- 100% EAS Guaranteed
- Green Device Available
- G-S ESD Protection Diode Embedded

APPLICATION

- Vcore / MB
- POL Application
- SMPS 2nd SR

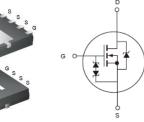
KEY PERFORMANCE PARAMETERS			
PARAMETER		VALUE	UNIT
V_{DS}		30	V
R _{DS(on)} (max)	$V_{GS} = 10V$	8	•
	$V_{GS} = 4.5V$	12.5	mΩ
Q_{g}		7.5	nC











Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	l _D	55	Α	
Continuous Drain Current	T _C = 100°C		35		
Pulsed Drain Current (Note 2)		I _{DM}	220	А	
Total Power Dissipation @ T _C = 25°C		P_{DTOT}	54	W	
Single Pulsed Avalanche Energy (Note 3)		E_AS	45	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	30	А	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	2.3	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W	

Notes: R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{eJA} is guaranteed by design while R_{eCA} is determined by the user's board design. R_{eJA} shown below for single device operation on FR-4 PCB in still air.



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)		•				
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.6	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±10	μA
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 16A$			6.5	8	mΩ
	$V_{GS} = 4.5V, I_D = 8A$	$R_{DS(on)}$		9.5	12.5	mΩ
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 15V, I_{D} = 20A,$ $V_{GS} = 4.5V$	Q_g		7.5		
Gate-Source Charge		Q_gs		1.3		nC
Gate-Drain Charge		Q_{gd}		4.5		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		750		
Output Capacitance		C _{oss}		150		pF
Reverse Transfer Capacitance		C _{rss}		110		
Gate Resistance	F = 1MHz, open drain	R_g		2.7		Ω
Switching (Note 6)		•				
Turn-On Delay Time		t _{d(on)}		4.8		
Turn-On Rise Time	$V_{DD} = 15V,$ $R_{GEN} = 3.3\Omega,$ $I_{D} = 15A, V_{GS} = 10V,$	t _r		12.5		
Turn-Off Delay Time		t _{d(off)}		27.6		ns
Turn-Off Fall Time		t _f		8.2		
Source-Drain Diode (Note 4)						
Forward On Voltage	I _S = 1A, V _{GS} = 0V	V _{SD}			1	V

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L=0.1mH, $I_{AS}=30A$, $V_{DD}=25V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.



Taiwan Semiconductor

ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM080N03EPQ56 RLG	PDFN56	2,500pcs / 13" Reel

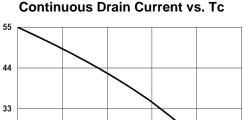
Note:

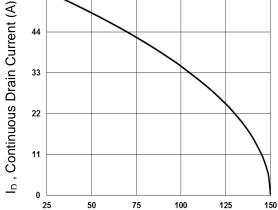
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



CHARACTERISTICS CURVES

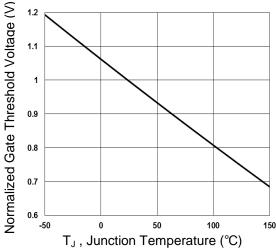
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



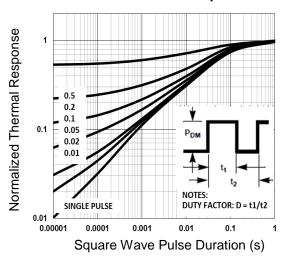




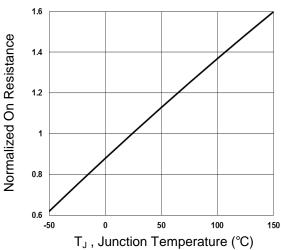
T_C, Case Temperature (°C)



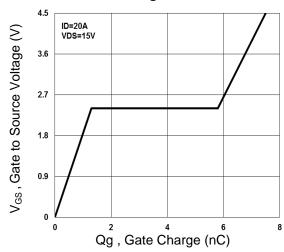
Normalized Transient Impedance



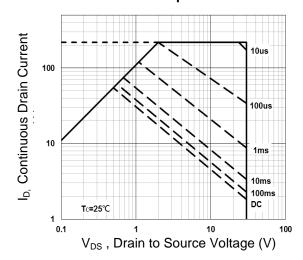
Normalized RDSON vs. T_J



Gate Charge Waveform

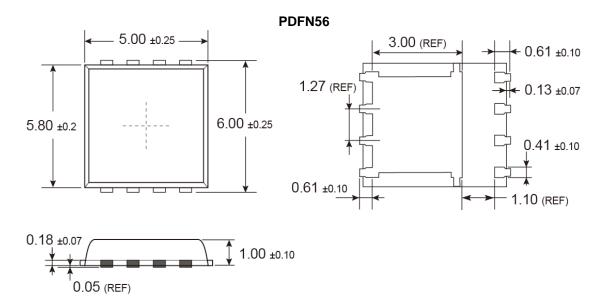


Maximum Safe Operation Area

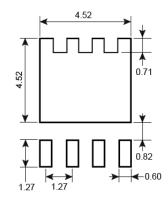




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

 $L = \text{Lot Code } (1\sim9, A\sim Z)$



Taiwan Semiconductor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.